

Description

Advanced process capability and packaging maximize the power handling and performance of this small outline transistor. The reverse blocking capability of the transistor can often result in the elimination of a series connected Schottky diode commonly required with either bipolar transistors or MOSFETs when used in battery charging applications.

Features

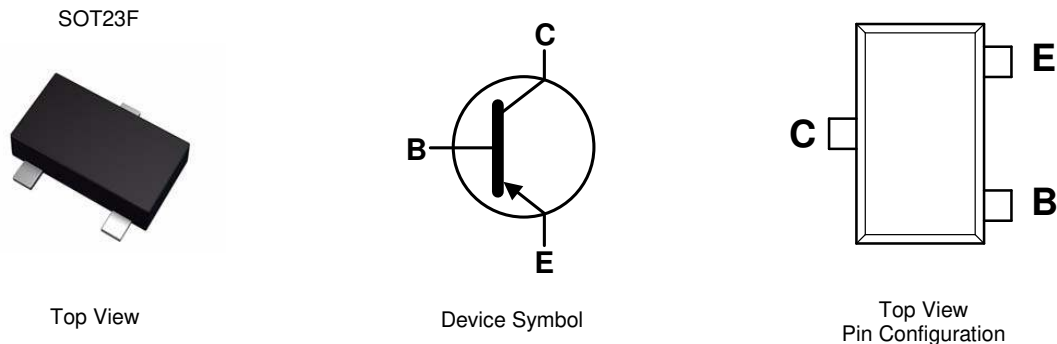
- $BV_{CEO} > -20V$
- $BV_{ECO} > -7V$
- $I_C = -4.5A$ Continuous Collector Current
- Low Saturation Voltage $V_{CE(SAT)} < -65mV @ -1A$
- $R_{CE(SAT)} = 41m\Omega$
- h_{FE} Characterised Up to $-10A$
- 1.5W Power Dissipation
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

Mechanical Data

- Case: SOT23F
- Case Material: Molded Plastic. "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 (E3)
- Weight: 0.012 grams (Approximate)

Applications

- Mobile Phone Charging Circuits
- MOSFET and IGBT Gate Drivers
- High-Side Driving
- Motor Control
- Disconnect Switch in Portable Products
- DC-DC Convertors

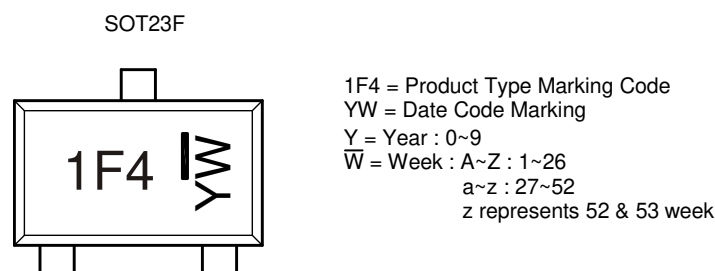


Ordering Information (Note 4)

Product	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
ZXTP25020CFFTA	AEC-Q101	1F4	7	8	3,000

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information



Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CB0}	-25	V
Collector-Emitter Voltage	V _{CEO}	-20	V
Emitter-Collector Voltage (Reverse Blocking)	V _{ECO}	-7	V
Emitter-Base Voltage	V _{EBO}	-7	V
Continuous Collector Current	I _C	-4.5	A
Peak Pulse Current	I _{CM}	-10	A
Base Current	I _B	-1	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

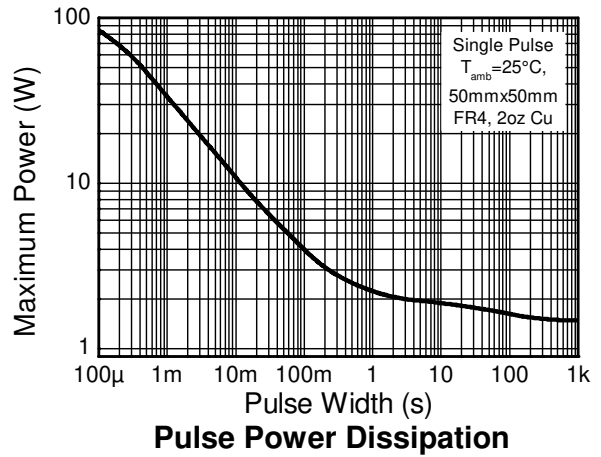
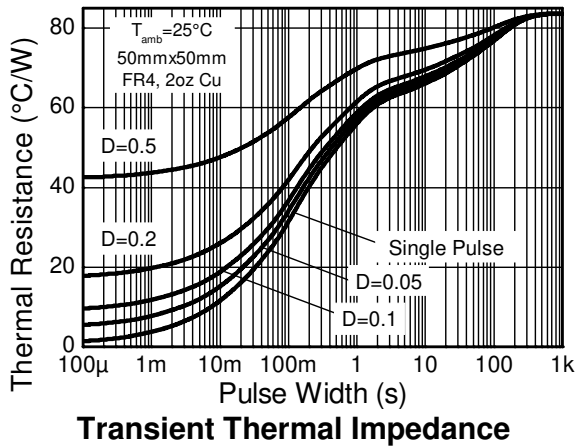
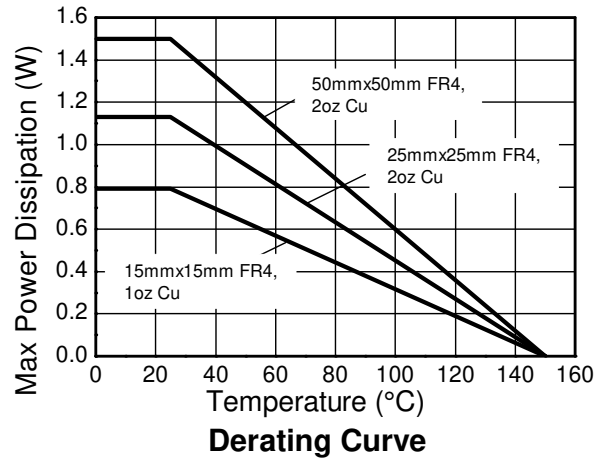
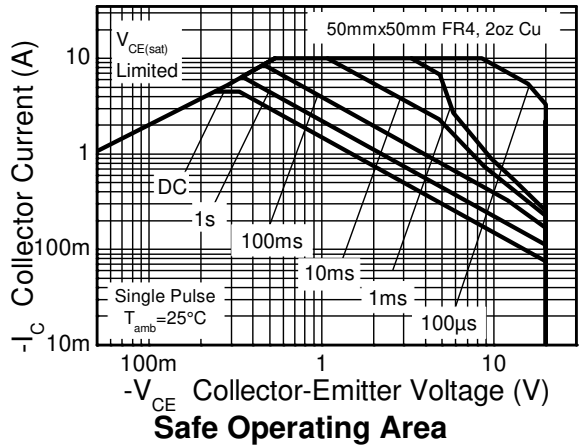
Characteristic	Symbol	Value	Unit
Power Dissipation Linear Derating Factor	P _D	0.79	W mW/°C
		6.3	
		1.13	
		9.0	
		1.50	
Thermal Resistance, Junction to Ambient	R _{θJA}	12.0	°C/W
		1.96	
		15.7	
		158.7	
Thermal Resistance, Junction to Ambient	R _{θJA}	110.4	°C/W
		83.3	
		63.7	
Thermal Resistance, Junction to Lead	R _{θJL}	60	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

ESD Ratings (Note 10)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge – Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge – Machine Model	ESD MM	400	V	C

- Notes:
- For a device mounted with the exposed collector pad on 15mm x 15mm 1oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
 - Same as Note 5, except the device is mounted on 25mm x 25mm 2oz copper.
 - Same as Note 5, except the device is mounted on 50mm x 50mm 2oz copper.
 - Same as Note 7, whilst measured at t < 5 seconds.
 - Thermal resistance from junction to solder-point (at the end of the collector lead).
 - Refer to JEDEC specification JESD22-A114 and JESD22-A115.

Thermal Characteristics and Derating Information

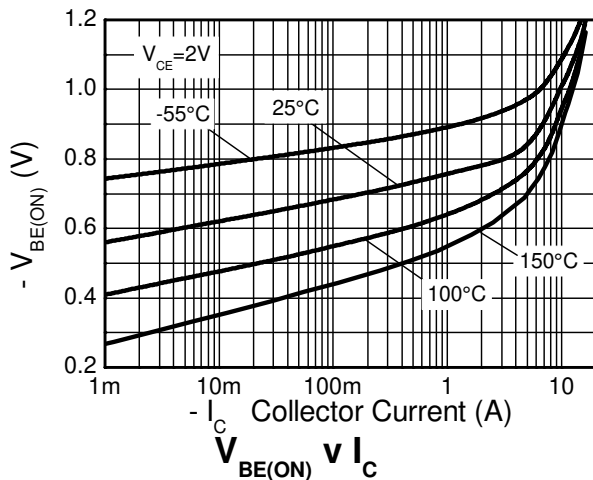
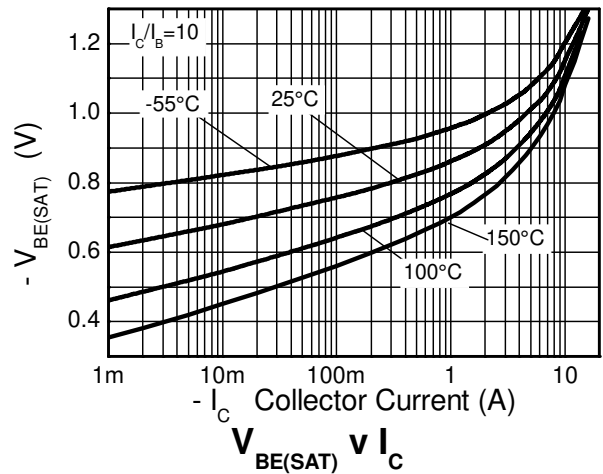
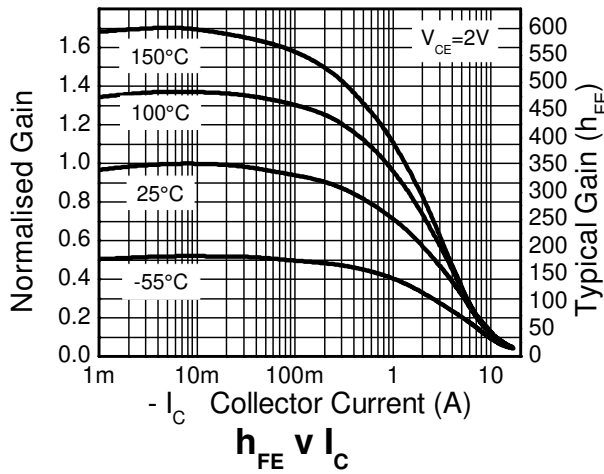
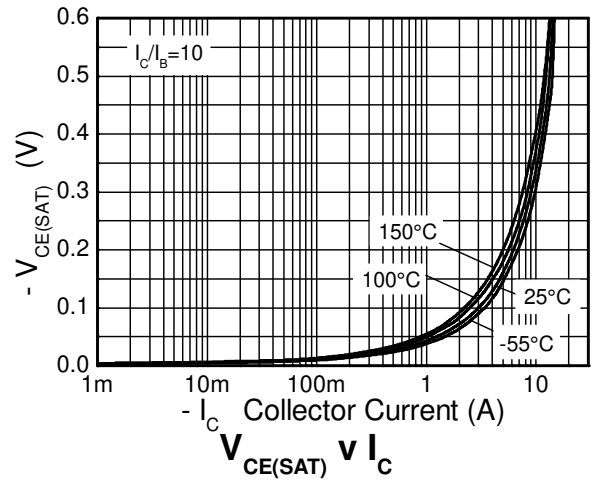
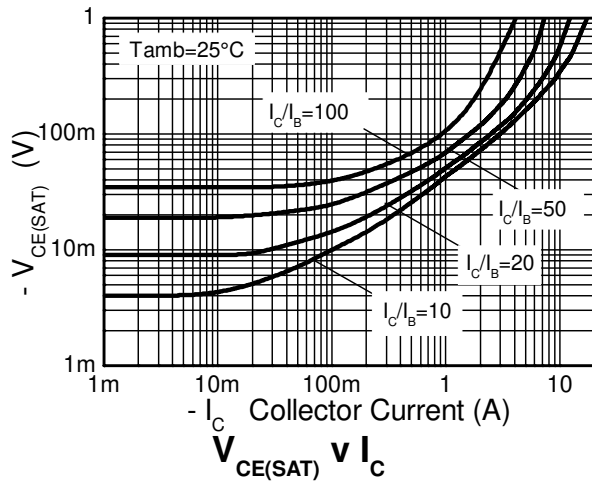


Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS						
Collector-Base Breakdown Voltage	BV _{CBO}	-25	-50	—	V	I _C = -100μA
Collector-Emitter Breakdown Voltage (Base Open) (Note 11)	BV _{CEO}	-20	-35	—	V	I _C = -10mA
Emitter-Base Breakdown Voltage	BV _{EBO}	-7	-8.2	—	V	I _E = -100μA
Emitter-Collector Breakdown Voltage (Reverse Blocking) (Note 11)	BV _{ECX}	-7	-8.0	—	V	I _E = -100μA R _{BC} < 10kΩ or -0.25V < V _{BC} < 0.25V
Emitter-Collector Breakdown Voltage (Base Open) (Note 11)	BV _{ECO}	-7	-8.8	—	V	I _E = -100μA
Collector-Base Cutoff Current	I _{CBO}	—	<-1	-50	nA	V _{CB} = -20V
Emitter-Base Cutoff Current	I _{EBO}	—	<-1	-50	nA	V _{CB} = -20V, T _A = +100°C
ON CHARACTERISTICS (Note 11)						
Static Forward Current Transfer Ratio	h _{FE}	200 150 85 —	350 250 140 40	500 — — —	—	I _C = -10mA, V _{CE} = -2V I _C = -1A, V _{CE} = -2V I _C = -4A, V _{CE} = -2V I _C = -10A, V _{CE} = -2V
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	—	-50 -80 -135 -210	-65 -110 -185 -260	mV	I _C = -1A, I _B = -100mA I _C = -1A, I _B = -20mA I _C = -2A, I _B = -40mA I _C = -4.5A, I _B = -225mA
Base-Emitter Saturation Voltage	V _{BE(SAT)}	—	-950	-1,050	mV	I _C = -4.5A, I _B = -225mA
Base-Emitter On Voltage	V _{BE(ON)}	—	-840	-950	mV	I _C = -4.5A, V _{CE} = -2V
SMALL SIGNAL CHARACTERISTICS						
Transition Frequency	f _T	—	285	—	MHz	I _C = -50mA, V _{CE} = -10V, f = 100MHz
Output Capacitance	C _{OBO}	—	32.4	40	pF	V _{CB} = -10V, f = 1MHz
Delay Time	t _D	—	38.4	—	ns	V _{CC} = -15V, I _C = -750mA, I _{B1} = I _{B2} = -15mA
Rise Time	t _R	—	49.2	—	ns	
Storage Time	t _S	—	168	—	ns	
Fall Time	t _F	—	55	—	ns	

Note: 11. Measured under pulsed conditions. Pulse width ≤ 300μs. Duty cycle ≤ 2%.

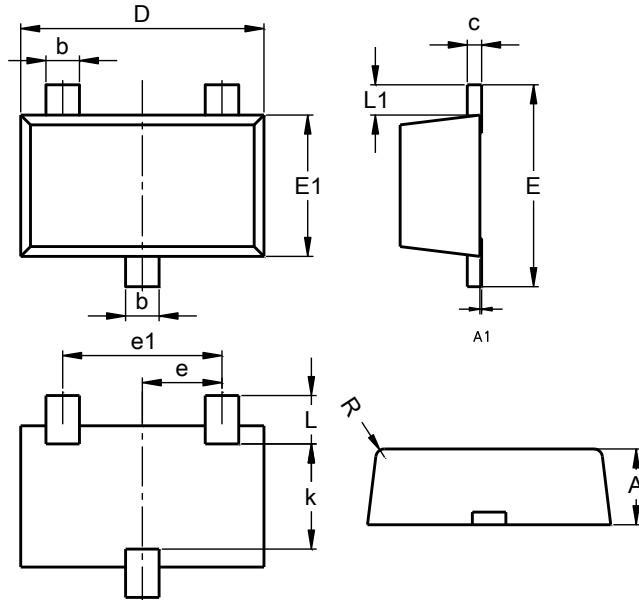
Typical Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)



Package Outline Dimensions

Please see AP02001 at http://www.diodes.com/_files/datasheets/ap02001.pdf for the latest version.

SOT23F

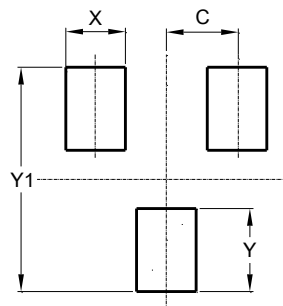


SOT23F			
Dim	Min	Max	Typ
A	0.80	1.00	0.90
b	0.35	0.50	0.44
c	0.10	0.20	0.16
D	2.80	3.00	2.90
e	0.95 REF		
e1	0.190 REF		
E	2.30	2.50	2.40
E1	1.50	1.70	1.65
k	1.20	-	-
L	0.30	0.65	0.50
L1	0.30	0.50	0.40
R	0.05	0.15	-
All Dimensions in mm			

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/_files/datasheets/ap02001.pdf for the latest version.

SOT23F



Dimensions	Value (in mm)
C	0.95
X	0.80
Y	1.110
Y1	3.000

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